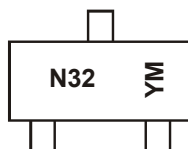


## Marking Information



N32 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: I = 2021)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2012	.....	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Z	.....	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	I <sub>D</sub>	4.0	A
Body-Diode Continuous Current (Note 5)	I <sub>S</sub>	1.5	A

## Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	90	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.6	—	1.4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	52 65 85	m $\Omega$	$V_{GS} = 10V, I_D = 4A$ $V_{GS} = 4.5V, I_D = 3A$ $V_{GS} = 2.5V, I_D = 2A$
Forward Transconductance	$ Y_{fs} $	—	6.6	—	S	$V_{DS} = 5V, I_D = 3.1A$
Source-Drain Diode Forward Voltage	$V_{SD}$	—	—	1.16	V	$V_{GS} = 0V, I_S = 2.0A$
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Gate Resistance	$R_g$	—	2.2	—	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (10V)	$Q_g$	—	11.7	—	nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 4A$
Total Gate Charge (4.5V)	$Q_g$	—	5.5	—	nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 4A$
Gate-Source Charge	$Q_{gs}$	—	1.1	—	nC	
Gate-Drain Charge	$Q_{gd}$	—	1.8	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	1.9	—	ns	$V_{DD} = 15V, V_{GEN} = 10V, R_{GEN} = 3\Omega, R_L = 3.75\Omega$
Turn-On Rise Time	$t_r$	—	1.6	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	10.3	—	ns	
Turn-Off Fall Time	$t_f$	—	2.0	—	ns	
Input Capacitance	$C_{iss}$	—	464	—	pF	$V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	49.5	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	43.8	—	pF	

Notes: 5. Device mounted on FR-4 PCB.  $t \leq 5$  sec.  
6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to production testing.

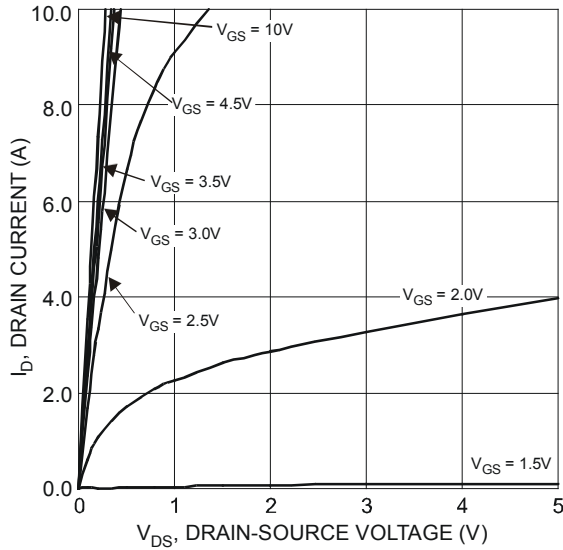


Figure 1 Typical Output Characteristics

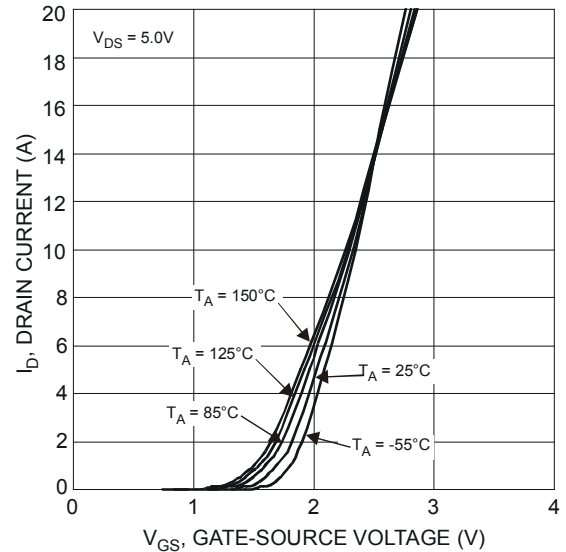


Figure 2 Typical Transfer Characteristics

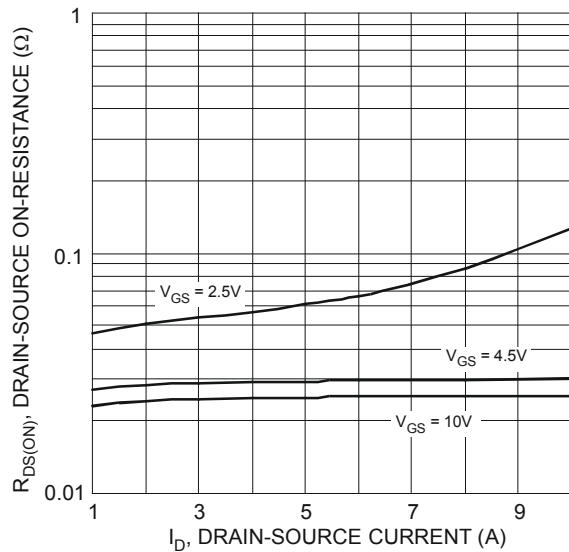


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

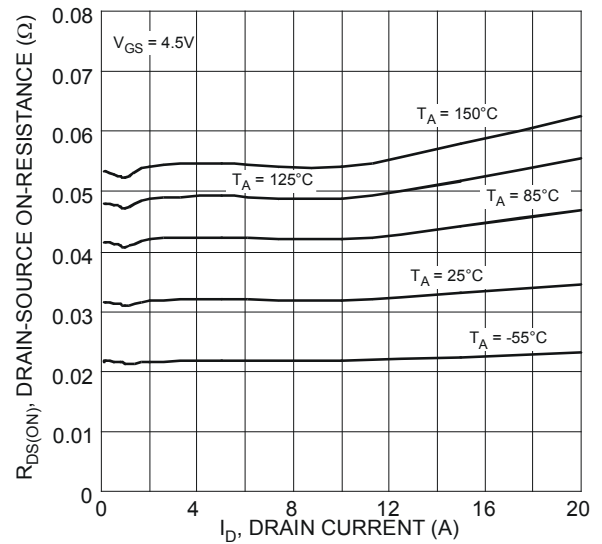


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

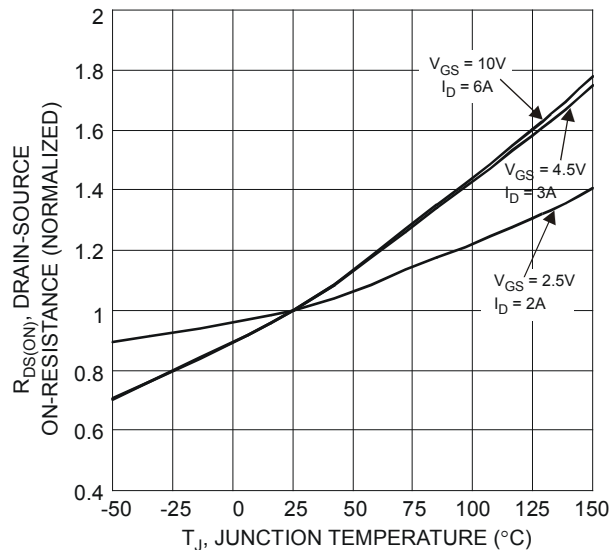


Figure 5 On-Resistance Variation with Temperature

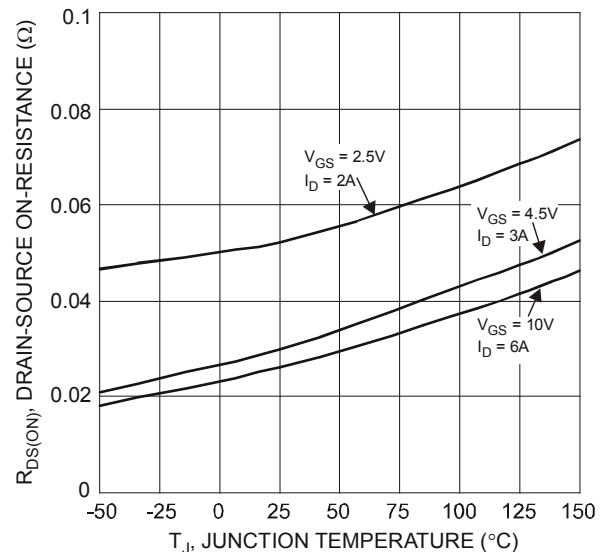


Figure 6 On-Resistance Variation with Temperature

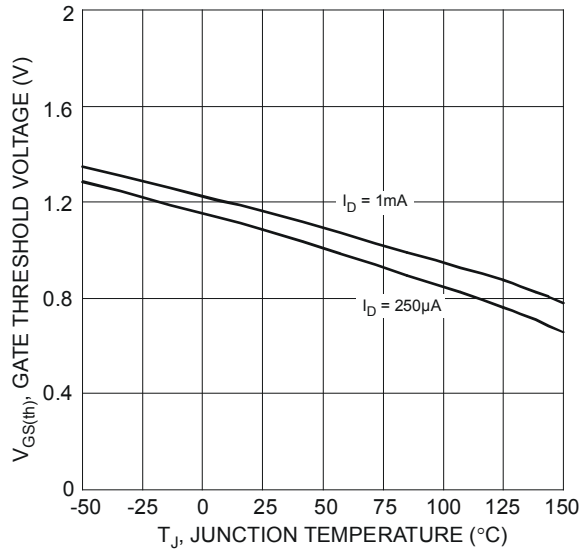


Figure 7 Gate Threshold Variation vs. Ambient Temperature

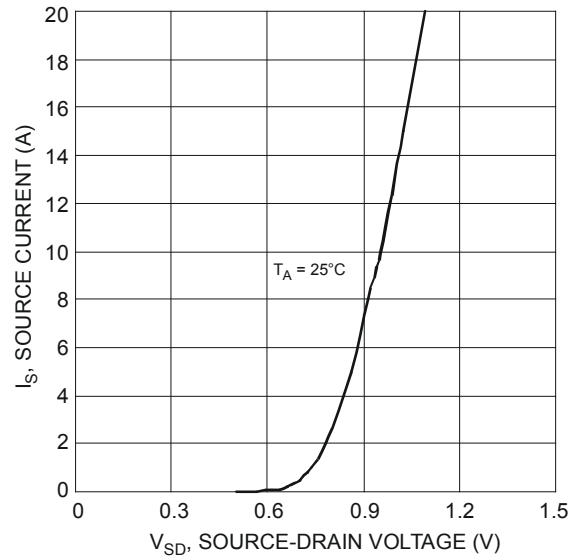


Figure 8 Diode Forward Voltage vs. Current

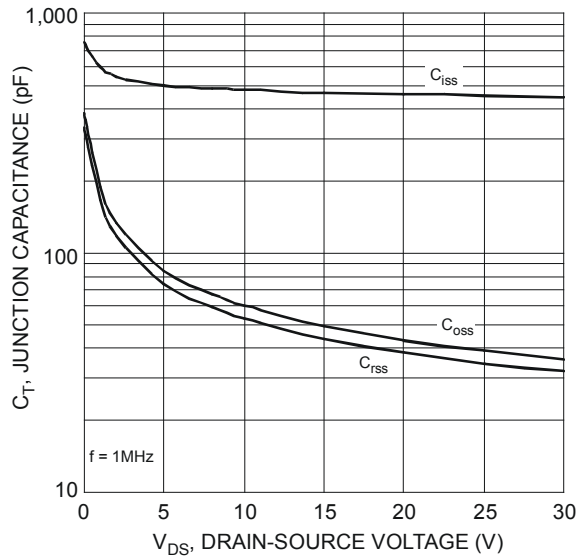


Figure 9 Typical Junction Capacitance

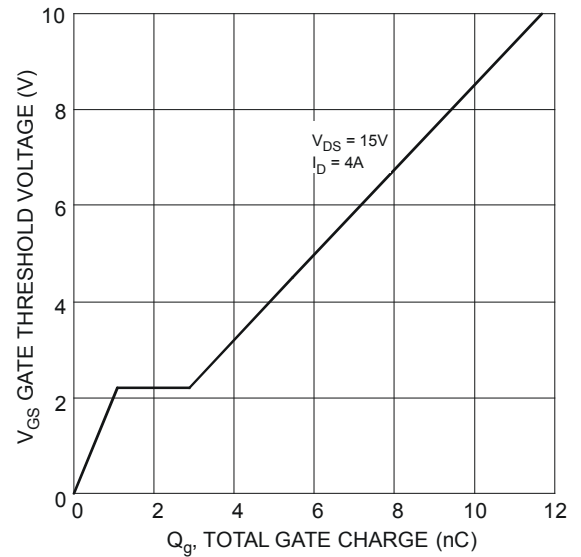


Figure 10 Gate Charge

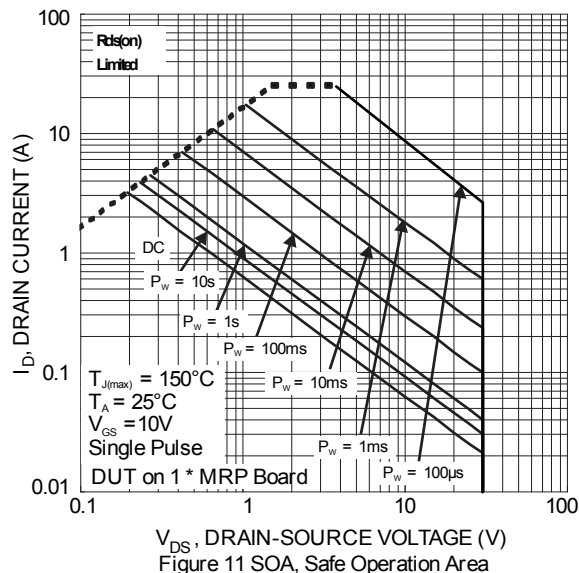
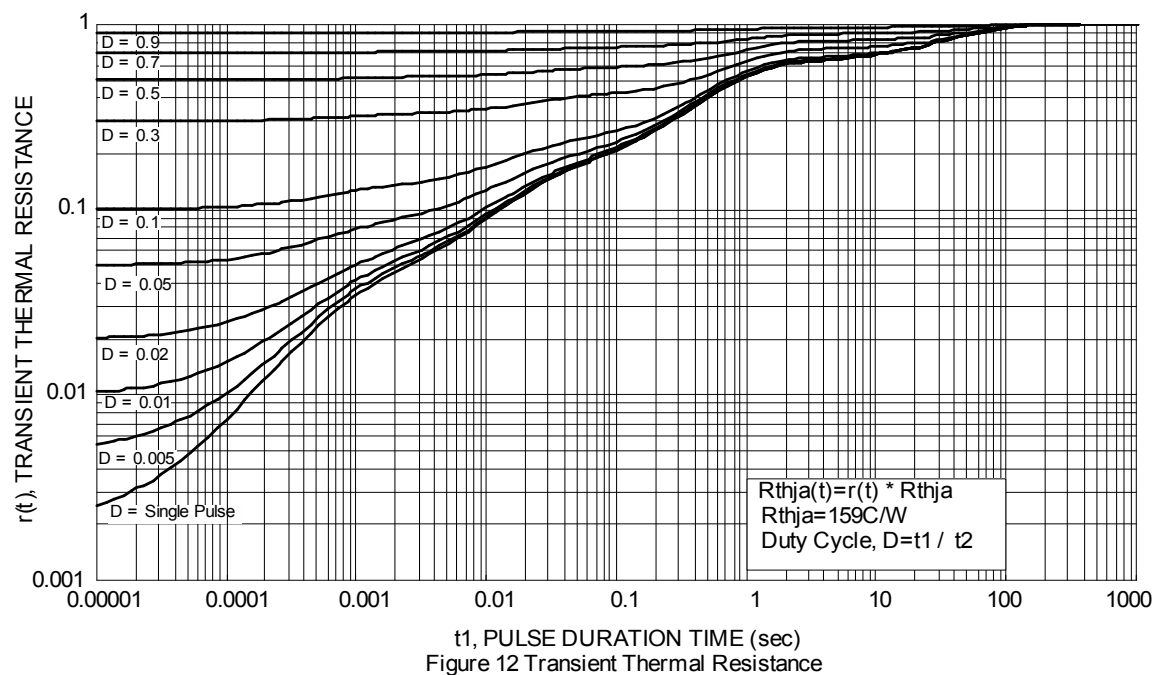


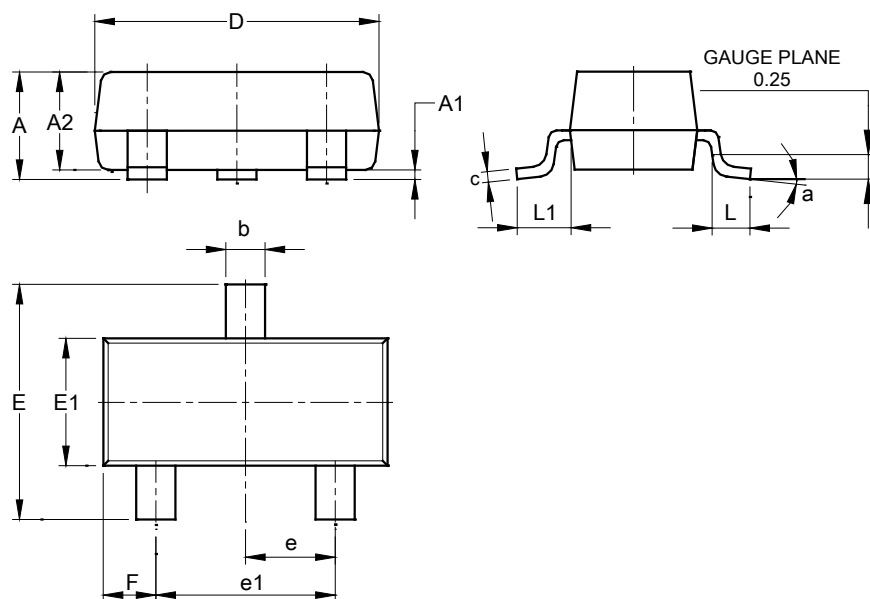
Figure 11 SOA, Safe Operation Area



## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23 (Standard)

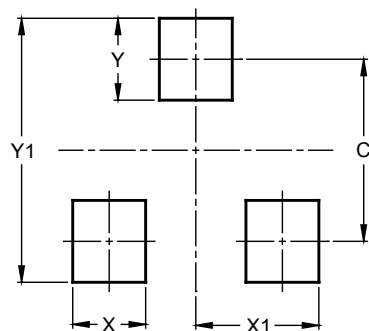


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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